

# BCR2PM-12RE

Triac

Low Power Use

REJ03G1468-0100

Rev.1.00

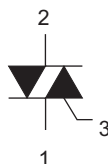
Jul 31, 2006

## Features

- $I_{T(RMS)}$  : 2 A
- $V_{DRM}$  : 600 V
- $I_{RGT1}, I_{RGT}$  : 10 mA
- Insulated Type
- Planar Passivation Type
- The product guaranteed maximum junction temperature 150°C.

## Outline

RENESAS Package code: PRSS0003AA-B  
(Package name: TO-220F(2) )



1. T<sub>1</sub> Terminal
2. T<sub>2</sub> Terminal
3. Gate Terminal

## Applications

Electric rice cooker, electric pot, and controller for other heater

## Precautions on Usage

When the BCR2PM-12RE is used, do not attach the heat radiating fin.

## Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600	V
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	720	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_T$ (RMS)	2	A	Commercial frequency, sine full wave 360° conduction
Surge on-state current	$I_{TSM}$	10	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
$I^2t$ for fusing	$I^2t$	0.41	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	1	W	
Average gate power dissipation	$P_{G(AV)}$	0.1	W	
Peak gate voltage	$V_{GM}$	6	V	
Peak gate current	$I_{GM}$	1	A	
Junction temperature	$T_j$	- 40 to +150	°C	
Storage temperature	$T_{stg}$	- 40 to +150	°C	
Mass	—	2.0	g	Typical value

Notes: 1. Gate open.

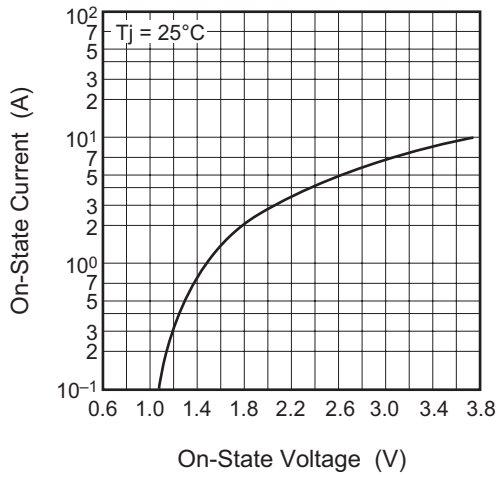
## Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	$I_{DRM}$	—	—	1.0	mA	$T_j = 150^\circ\text{C}$ , $V_{DRM}$ applied
On-state voltage	$V_{TM}$	—	—	1.6	V	$T_j = 25^\circ\text{C}$ , $I_{TM} = 1.5\text{ A}$ , Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	II	$V_{RGTI}$	—	—	2.0	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	III	$V_{RGTIII}$	—	—	2.0	
Gate trigger current <sup>Note2</sup>	II	$I_{RGTI}$	—	—	10	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	III	$I_{RGTIII}$	—	—	10	
Gate non-trigger voltage	$V_{GD}$	0.1	—	—	V	$T_j = 150^\circ\text{C}$ , $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-a)}$	—	—	45	°C/W	Junction to ambient, Natural convection

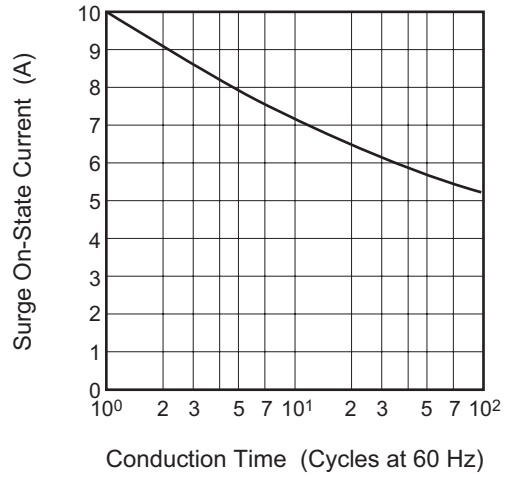
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

Performance Curves

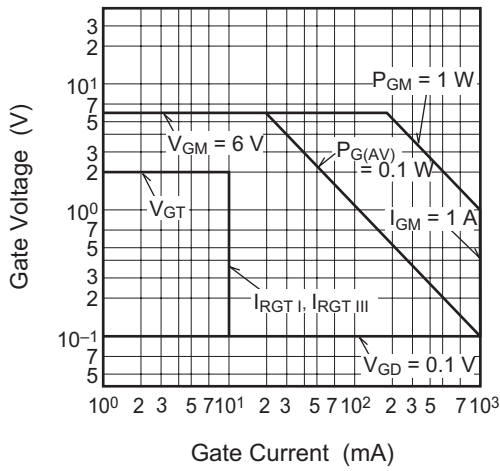
Maximum On-State Characteristics



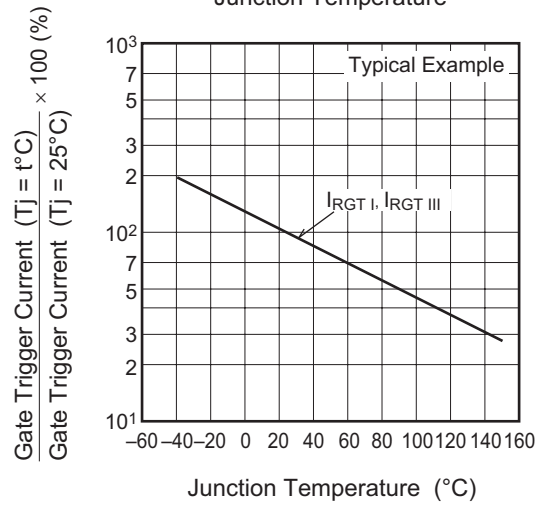
Rated Surge On-State Current



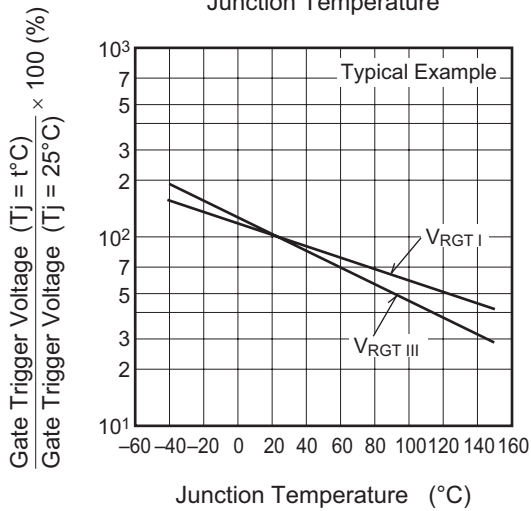
Gate Characteristics (II and III)



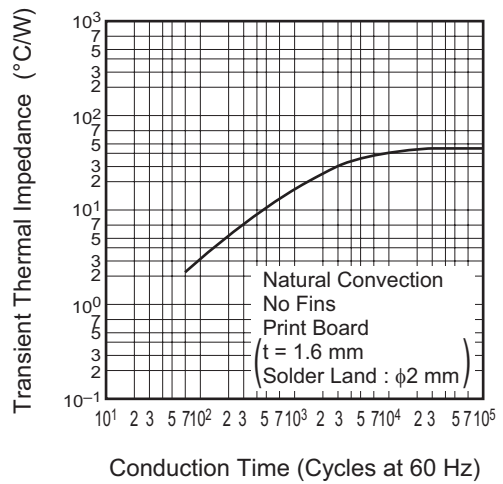
Gate Trigger Current vs. Junction Temperature

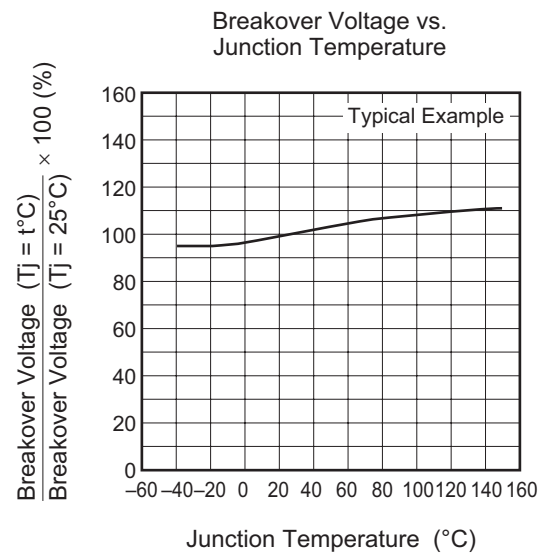
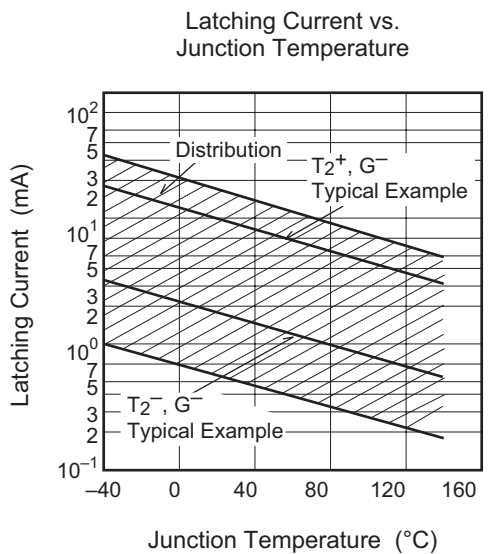
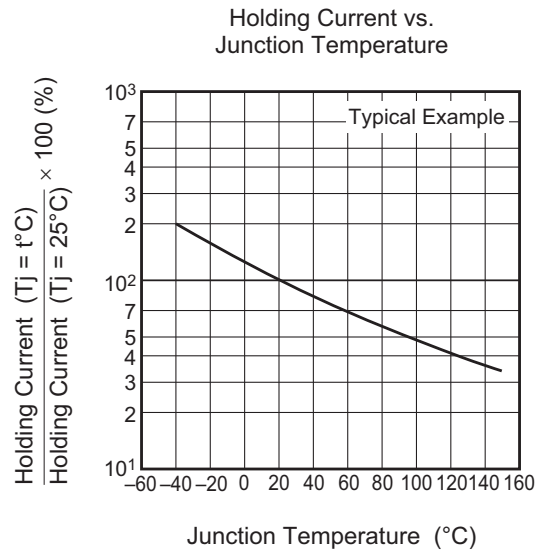
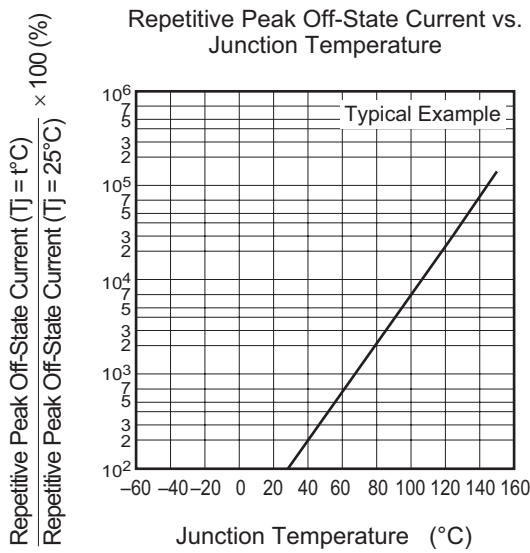
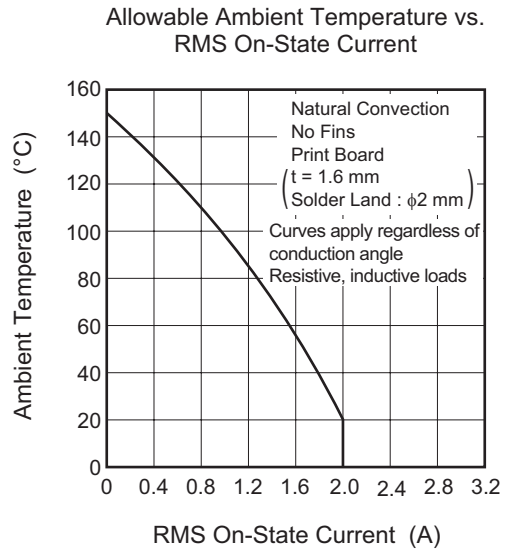
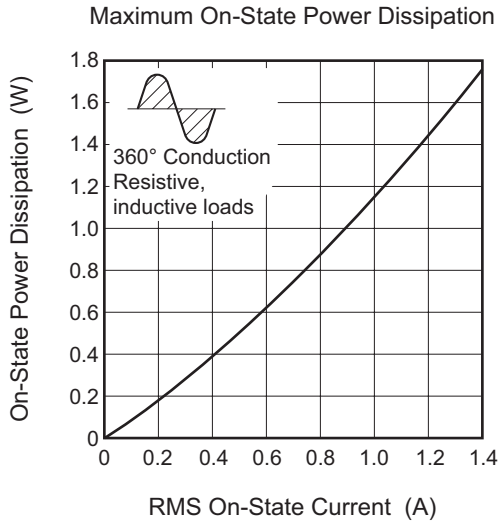


Gate Trigger Voltage vs. Junction Temperature

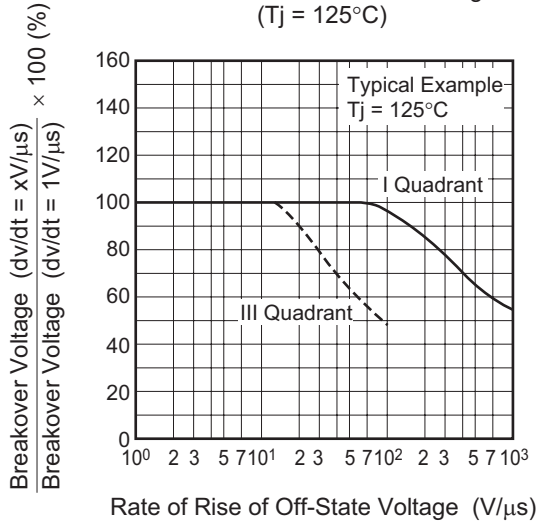


Maximum Transient Thermal Impedance Characteristics (Junction to ambient)

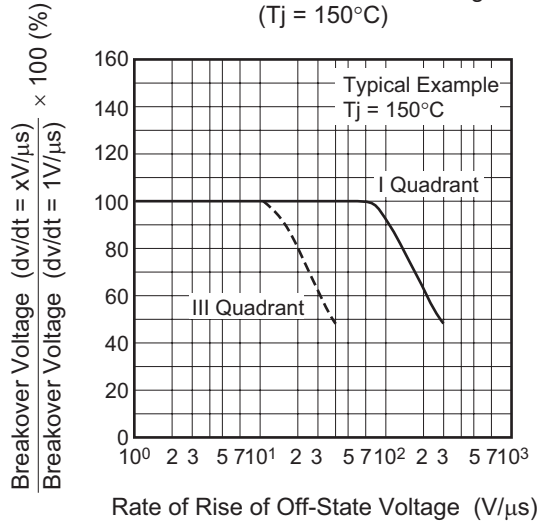




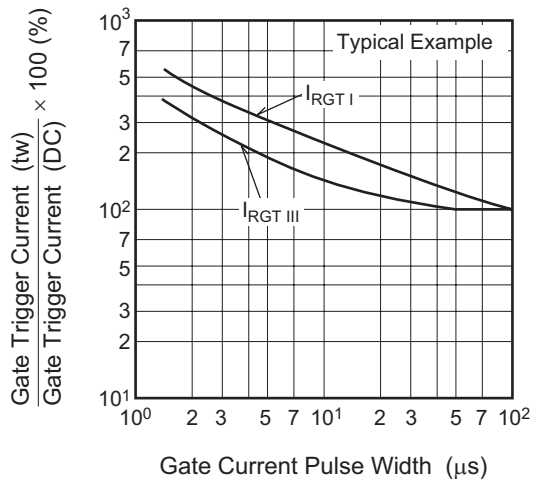
Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj = 125°C)



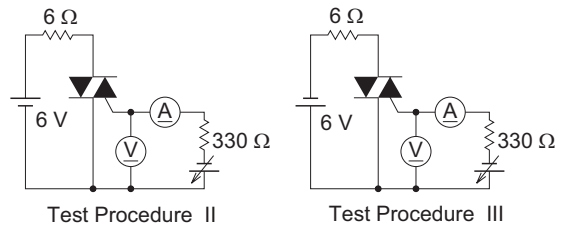
Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj = 150°C)



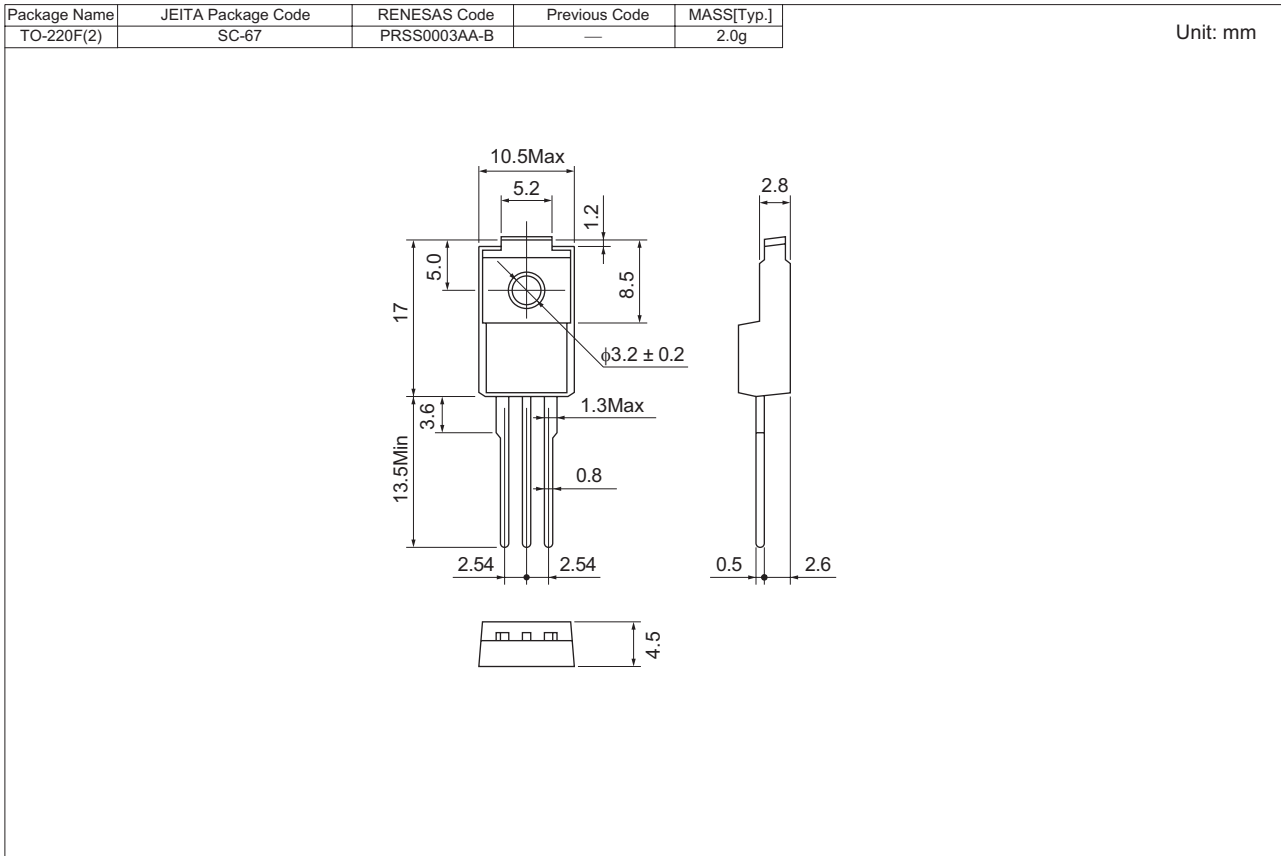
Gate Trigger Current vs. Gate Current Pulse Width



Gate Trigger Characteristics Test Circuits



Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR2PM-12RE
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR2PM-12RE-A8

Note : Please confirm the specification about the shipping in detail.

**Keep safety first in your circuit designs!**

1. Renesas Technology Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.  
Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

**Notes regarding these materials**

1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corp. product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corp. or a third party.
  2. Renesas Technology Corp. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
  3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corp. without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor for the latest product information before purchasing a product listed herein.  
The information described here may contain technical inaccuracies or typographical errors.  
Renesas Technology Corp. assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.  
Please also pay attention to information published by Renesas Technology Corp. by various means, including the Renesas Technology Corp. Semiconductor home page (<http://www.renesas.com>).
  4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corp. assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
  5. Renesas Technology Corp. semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
  6. The prior written approval of Renesas Technology Corp. is necessary to reprint or reproduce in whole or in part these materials.
  7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.  
Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
  8. Please contact Renesas Technology Corp. for further details on these materials or the products contained therein.
- 



**RENESAS SALES OFFICES**

<http://www.renesas.com>

Refer to "<http://www.renesas.com/en/network>" for the latest and detailed information.

**Renesas Technology America, Inc.**

450 Holger Way, San Jose, CA 95134-1368, U.S.A  
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

**Renesas Technology Europe Limited**

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.  
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

**Renesas Technology (Shanghai) Co., Ltd.**

Unit 204, 205, AZIAcenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120  
Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

**Renesas Technology Hong Kong Ltd.**

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong  
Tel: <852> 2265-6688, Fax: <852> 2730-6071

**Renesas Technology Taiwan Co., Ltd.**

10th Floor, No.99, Fushing North Road, Taipei, Taiwan  
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

**Renesas Technology Singapore Pte. Ltd.**

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632  
Tel: <65> 6213-0200, Fax: <65> 6278-8001

**Renesas Technology Korea Co., Ltd.**

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea  
Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

**Renesas Technology Malaysia Sdn. Bhd**

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia  
Tel: <603> 7955-9390, Fax: <603> 7955-9510